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`(_	MAY 1 0 2004 S IN THE UNITED STATES	S PATENT AND TRADEMARK OFFICE
/3		Group Art Unit
•	TRADEMARK.	Examiner: Ngar
	In re PATENT APPLICATION of	

Applicant	:	Mu-Jen LAI et al.)
Appl. No.	:	10/603,659)
Filed	:	June 26, 2003) INFORMATION) DISCLOSURE
For	:	WHITE LIGHT LED) STATEMENT)
Allowed	:	March 10, 2004)
Atty. Dkt.	:	SUND 466) .)

Mail Stop ISSUE FEE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

This is an information disclosure statement submitted in compliance with the timing requirements of 37 C.F.R. §1.97(b)(3), i.e., prior to a first Office Action on the merits.

Attached are copies of two English-language articles, which are listed on the attached Form PTO-1449. Any relevance of the articles is self-evident. The articles were first cited by Taiwanese Patent Office on March 23, 2004.

Since this Information Disclosure Statement is being filed before a first Office Action, no certification or fee is required, and the requirements of 37 C.F.R. §§1.97 and 1.98 are deemed to be fully met as to all documents listed. Consideration of the listed documents respectfully is requested.

Respectfully submitted,

May 10, 2004 Date

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SMR:vm



FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				Atty. Docket	Application No.				
			ATEMENT	SUND 466	10/603,659				
				Applicant Mu-Jen LAI et al.					
				Filing Date Group June 26, 2003 2814		1			
U.S. PATENT DOCUMENTS									
Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date		
	AA		,				<u> </u>		
	AB								
	AC								
	AD								
	AE								
	AF								
	AG								
	АН								
FOREIGN PATENT DOCUMENTS									
		Document Number	Date	Country	Class	Sub- Class	Trans- lation		
	Al								
	AJ								
	AK								
	AL								
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)									
	AM	"ZnTe-GaN heterostructure switching device", A. G. Drizhuk et al.; Tech. Phys. Lett. 23 (10), October 1997; 1997 American Institute of Physics; pages 809 and 810							
	AN	"Growth of GaN on Si substrates – roles of BP thin layer" OpticalMaterials, S. Nishimura et al.; one page – ISI Web of Science 6.0							
Examiner Date Considered									
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.									